L Number	Hits	Search Text	DB	Time stamp
21	1	6335292.pn.	USPAT	2004/02/05 14:23
22	313	Li-Li.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:23
23	41	Howard-Bradley-J.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:24
24	105	Li-Li.in. and @ay<=1999	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:24
25	189	(plasma and semiconductor and (etching same (oxide or SiO or SiO?sub.2))) and (second adj power)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:25
26	613	(CF?sub.4 with CHF?sub.3 with (inert or argon or argon or helium or he)) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:27
28	523	((CF?sub.4 with CHF?sub.3 with (inert or argon or argon or helium or he)) and plasma) and @ay<=2001	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:27
29	357	(((CF?sub.4 with CHF?sub.3 with (inert or argon or argon or helium or he)) and plasma) and @ay<=2001) and power	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:28
30	328	((((CF?sub.4 with CHF?sub.3 with (inert or argon or argon or helium or he)) and plasma) and @ay<=2001) and power) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:28
31	284	(((((CF?sub.4 with CHF?sub.3 with (inert or argon or argon or helium or he)) and plasma) and @ay<=2001) and power) and semiconductor) and ((etch or etching) same (SiO or siO?sub.2 or oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:29
32	222	((((((CF?sub.4 with CHF?sub.3 with (inert or argon or argon or helium or he)) and plasma) and @ay<=2001) and power) and semiconductor) and ((etch or etching) same (SiO or siO?sub.2 or oxide) same plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:29
-	1	6159794.pn.	USPAT	2003/01/08 09:16
-	17451	plasma and semiconductor and (etching same (oxide or SiO or SiO?sub.2))	USPAT	2003/04/16 13:04
-	160	(plasma and semiconductor and (etching same (oxide or SiO or SiO?sub.2))) and (second adj power)	USPAT	2004/02/05 14:24
-	124	((plasma and semiconductor and (etching same (oxide or SiO or SiO?sub.2))) and (second adj power)) and (chlorine or Cl?sub.2 or HBr or bromic or CF?sub.4 or CHF?sub.3 or "CH.sub.2 F.sub.2" or inert or argon or Ar or helium or he)	USPAT	2003/04/16 13:13

-	102	(((plasma and semiconductor and (etching same (oxide or SiO or SiO?sub.2))) and (second adj power)) and (chlorine or Cl?sub.2 or HBr or bromic or CF?sub.4 or CHF?sub.3 or "CH.sub.2 F.sub.2" or inert or argon or Ar or helium or he)) and (argon or Ar or helium or he)	USPAT	2003/01/08 13:09
-	2786	CF?sub.4 with CHF?sub.3	USPAT	2003/04/16 13:11
-	2247	(CF?sub.4 with CHF?sub.3) and plasma	USPAT	2003/04/16 13:09
-	452	CF?sub.4 with CHF?sub.3 with (inert or argon or argon or helium or he)	USPAT	2003/01/08 14:14
-	372	(CF?sub.4 with CHF?sub.3 with (inert or argon or argon or helium or he)) and plasma	USPAT	2004/02/05 14:26
-	260	((CF?sub.4 with CHF?sub.3 with (inert or argon or argon or helium or he)) and plasma) and power	USPAT	2003/01/08 13:10
-	223	(((CF?sub.4 with CHF?sub.3 with (inert or argon or argon or helium or he)) and plasma) and power) and ((etch or etching) same (oxide or SiO or SiO?sub.2))	USPAT	2003/01/08 14:26
-	188	((((CF?sub.4 with CHF?sub.3 with (inert or argon or argon or helium or he)) and plasma) and power) and ((etch or etching) same (oxide or SiO or SiO?sub.2))) and (watt or W)	USPAT	2003/01/08 13:12
-	183	(((((CF?sub.4 with CHF?sub.3 with (inert or argon or argon or helium or he)) and plasma) and power) and ((etch or etching) same (oxide or SiO or SiO?sub.2))) and (watt or W)) not (((plasma and semiconductor and (etching same (oxide or SiO or SiO?sub.2))) and (second adj power)) and (chlorine or Cl?sub.2 or HBr or bromic or CF?sub.4 or CHF?sub.3 or "CH.sub.2 F.sub.2" or inert or argon or Ar or helium or he))	USPAT	2003/01/08 13:12
-	201	CF?sub.4 with CHF?sub.3 with (helium or he)	USPAT	2003/01/08 14:15
-	2	((CF?sub.4 with CHF?sub.3 with (helium or he)) and plasma) and ((germanium or Ge) with substrate)	USPAT	2003/01/08 14:15
-	162	(CF?sub.4 with CHF?sub.3 with (helium or he)) and plasma	USPAT	2003/01/08 14:22
-	9465	(germanium with substrate) or (gallium with arsenide with substrate)	USPAT	2003/01/08 14:23
-	2021	((germanium or Ge) with substrate) and ((gallium or Ga) with (arsenide or As or GaAs) with substrate)	USPAT	2003/01/08 14:26
-	883	(((germanium or Ge) with substrate) and ((gallium or Ga) with (arsenide or As or GaAs) with substrate)) and plasma	USPAT	2003/01/08 14:26
-	1	6159794.pn. and ((etch or etching) same (oxide or SiO or SiO?sub.2))	USPAT	2003/01/08 14:27
-	378	((((germanium or Ge) with substrate) and ((gallium or Ga) with (arsenide or As or GaAs) with substrate)) and plasma) and ((etch or etching) same (oxide or SiO or SiO?sub.2))	USPAT	2003/01/08 14:27
-	210	(((((germanium or Ge) with substrate) and ((gallium or Ga) with (arsenide or As or GaAs) with substrate)) and plasma) and ((etch or etching) same (oxide or SiO or SiO?sub.2))) and power	USPAT	2003/01/08 16:19
-	40037	(etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)	USPAT	2003/04/16 13:08
-	19320	((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma	USPAT	2003/04/16 13:06

—	4689	(((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))	USPAT	2003/04/16 13:09
—	21441	(etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2)	USPAT	2003/04/16 13:08
—	3205	((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))	USPAT	2003/04/16 13:09
—	2225	(((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (Cl?sub.2 or Cl2 or HBr or hydro&1bromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")	USPAT	2003/04/16 13:10
—	664	((((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (Cl?sub.2 or Cl2 or HBr or hydro&1bromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)	USPAT	2003/04/16 13:11
—	541	(((((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (Cl?sub.2 or Cl2 or HBr or hydro&1bromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001	USPAT	2003/04/16 13:11
—	492	((((((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (Cl?sub.2 or Cl2 or HBr or hydro&1bromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001) and second	USPAT	2003/04/16 13:17
—	425	(((((((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (Cl?sub.2 or Cl2 or HBr or hydro&1bromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001) and second) and (inert or argon or Ar or helium or he)	USPAT	2003/04/16 13:14

–	192	((((((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (Cl?sub.2 or Cl2 or HBr or hydro&1bromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001) and (second with power)	USPAT	2003/04/16 13:17
–	179	((((((((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (Cl?sub.2 or Cl2 or HBr or hydro&1bromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001) and second) and (inert or argon or Ar or helium or he)) and (second with power)	USPAT	2003/04/16 13:28
–	192	((((((((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (Cl?sub.2 or Cl2 or HBr or hydro&1bromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001) and second) and (second with power)	USPAT	2003/04/16 13:28
–	60	((((((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (Cl?sub.2 or Cl2 or HBr or hydro&1bromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001) and (second near3 power)	USPAT	2003/04/16 13:47
–	2	5726449.pn. 5710067.pn.	USPAT	2003/04/16 13:48
–	2	5726499.pn. 5710067.pn.	USPAT	2003/04/16 14:34
–	1	6335292.pn.	USPAT	2003/04/16 15:08
–	1	6087269.pn.	USPAT	2003/04/16 15:08
–	1	6335292.pn.	USPAT	2003/10/10 10:04
–	0	Bradley-Howard.in.	USPAT; US-PGPUB	2003/10/10 10:04
–	0	Bradley-Howard-J.in.	USPAT; US-PGPUB	2003/10/10 10:05
–	208	Li-Li.in.	USPAT; US-PGPUB	2003/10/10 10:05
–	0	Li-Li.in. and plamsa	USPAT; US-PGPUB	2003/10/10 10:06
–	124	Li-Li.in. and (etch or etching)	USPAT; US-PGPUB	2003/10/10 10:07
–	87	Li-Li.in. and plasma	USPAT; US-PGPUB	2003/10/10 10:07
–	25	(Li-Li.in. and (etch or etching)) and (Li-Li.in. and plasma) and power	USPAT; US-PGPUB	2003/10/10 10:07

-	179	(plasma and semiconductor and (etching same (oxide or SiO or SiO?sub.2))) and (second adj power)	USPAT	2003/10/10 12:55
-	141	((plasma and semiconductor and (etching same (oxide or SiO or SiO?sub.2))) and (second adj power)) and @ay<=1999	USPAT	2003/10/10 12:54
-	1	6174451.pn.	USPAT	2003/10/10 11:59
-	109	(plasma and semiconductor and (etching same ((silicon adj oxide) or SiO or SiO?sub.2))) and (second adj power)	USPAT	2003/10/10 12:55
-	71	((plasma and semiconductor and (etching same ((silicon adj oxide) or SiO or SiO?sub.2))) and (second adj power)) and @ay<=1998	USPAT	2003/10/10 13:43
-	2	5726499.pn. 5710067.pn.	USPAT	2003/10/10 13:44

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